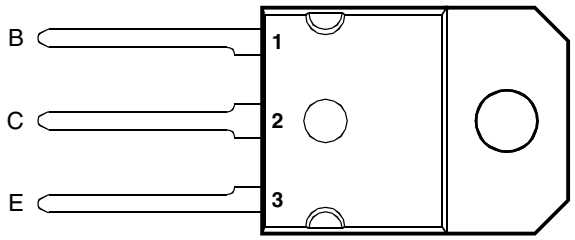
- **Rugged Triple-Diffused Planar Construction**
- **6 A Continuous Collector Current**
- **Operating Characteristics Fully Guaranteed at 100°C**
- **1000 Volt Blocking Capability**
- **120 W at 25°C Case Temperature**

SOT-93 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage (I_E = 0)	TIPL762 TIPL762A	V_{CBO}	850 1000	V
Collector-emitter voltage (V_{BE} = 0)	TIPL762 TIPL762A	V_{CES}	850 1000	V
Collector-emitter voltage (I_B = 0)	TIPL762 TIPL762A	V_{CEO}	400 450	V
Emitter-base voltage		V_{EBO}	10	V
Continuous collector current		I_C	6	A
Peak collector current (see Note 1)		I_{CM}	12	A
Continuous device dissipation at (or below) 25°C case temperature		P_{tot}	120	W
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C

NOTE 1: This value applies for $t_p \leq 10$ ms, duty cycle $\leq 2\%$.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS				MIN	TYP	MAX	UNIT
$V_{CEO(sus)}$	Collector-emitter sustaining voltage	I_C = 100 mA	L = 25 mH	(see Note 2)	TIPL762	400			V
					TIPL762A	450			
I_{CES}	Collector-emitter cut-off current	V_{CE} = 850 V	V_{BE} = 0		TIPL762			50	µA
		V_{CE} = 1000 V	V_{BE} = 0		TIPL762A			50	
		V_{CE} = 850 V	V_{BE} = 0	T_C = 100°C	TIPL762			200	
		V_{CE} = 1000 V	V_{BE} = 0	T_C = 100°C	TIPL762A			200	
I_{CEO}	Collector cut-off current	V_{CE} = 400 V	I_B = 0		TIPL762			50	µA
		V_{CE} = 450 V	I_B = 0		TIPL762A			50	
I_{EBO}	Emitter cut-off current	V_{EB} = 10 V	I_C = 0					1	mA
h_{FE}	Forward current transfer ratio	V_{CE} = 5 V	I_C = 0.5 A	(see Notes 3 and 4)		20		60	
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_B = 0.4 A	I_C = 2 A					0.5	V
		I_B = 0.8 A	I_C = 4 A	(see Notes 3 and 4)				1.0	
		I_B = 1.2 A	I_C = 6 A					2.5	
		I_B = 1.2 A	I_C = 6 A	T_C = 100°C				5.0	
$V_{BE(sat)}$	Base-emitter saturation voltage	I_B = 0.4 A	I_C = 2 A					1.1	V
		I_B = 0.8 A	I_C = 4 A	(see Notes 3 and 4)				1.3	
		I_B = 1.2 A	I_C = 6 A					1.5	
		I_B = 1.2 A	I_C = 6 A	T_C = 100°C				1.4	
f_t	Current gain bandwidth product	V_{CE} = 10 V	I_C = 0.5 A	f = 1 MHz			6		MHz
C_{ob}	Output capacitance	V_{CB} = 20 V	I_E = 0	f = 0.1 MHz			105		pF

NOTES: 2. Inductive loop switching measurement.
3. These parameters must be measured using pulse techniques, t_p = 300 µs, duty cycle ≤ 2%.
4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.25	°C/W

inductive-load-switching characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{sv}	Voltage storage time	I_C = 6 A $V_{BE(off)}$ = -10 V	$I_{B(on)}$ = 1.2 A	(see Figures 1 and 2)			2.5	µs
t_{rv}	Voltage rise time						200	ns
t_{fi}	Current fall time						150	ns
t_{ti}	Current tail time						50	ns
t_{xo}	Cross over time						300	ns
t_{sv}	Voltage storage time	I_C = 6 A $V_{BE(off)}$ = -10 V	$I_{B(on)}$ = 1.2 A T_C = 100°C	(see Figures 1 and 2)			3	µs
t_{rv}	Voltage rise time						300	ns
t_{fi}	Current fall time						150	ns
t_{ti}	Current tail time						50	ns
t_{xo}	Cross over time						500	ns

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PARAMETER MEASUREMENT INFORMATION

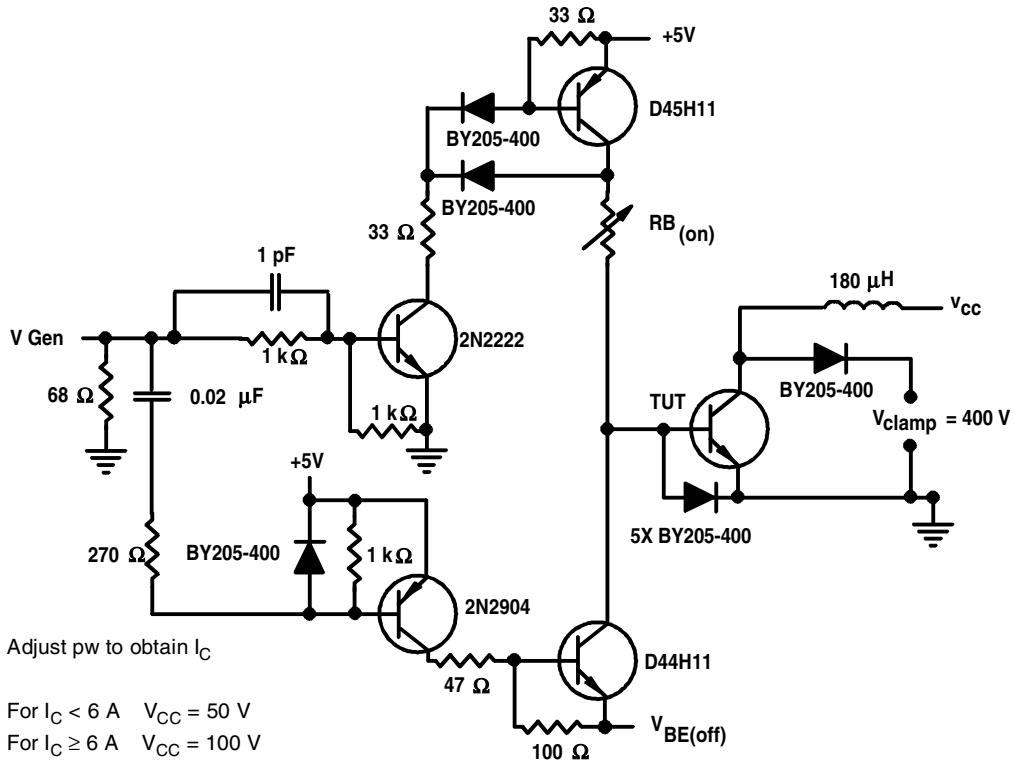
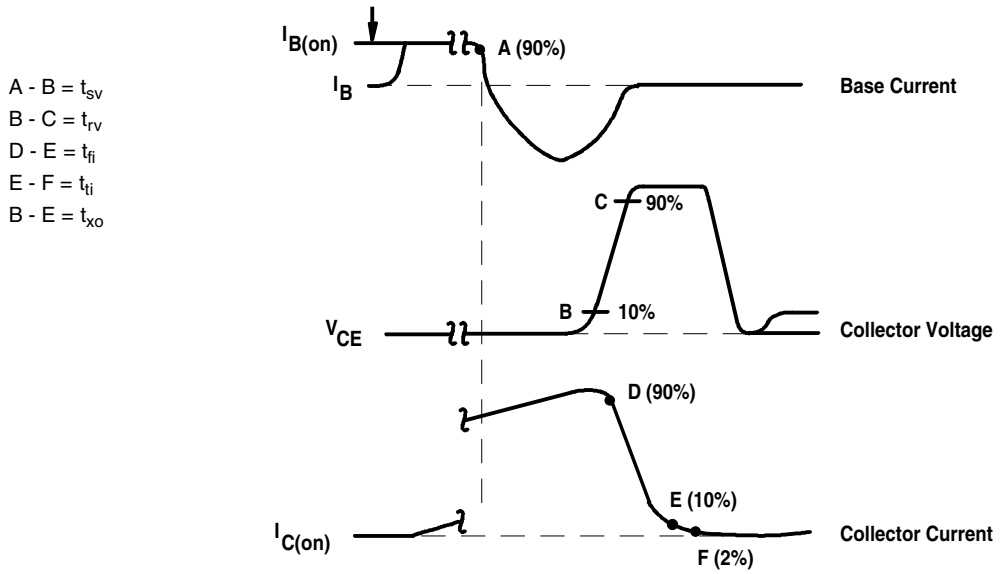


Figure 1. Inductive-Load Switching Test Circuit



NOTES: A. Waveforms are monitored on an oscilloscope with the following characteristics: t_r < 15 ns, R_{in} > 10 Ω, C_{in} < 11.5 pF.
B. Resistors must be noninductive types.

Figure 2. Inductive-Load Switching Waveforms

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs COLLECTOR CURRENT

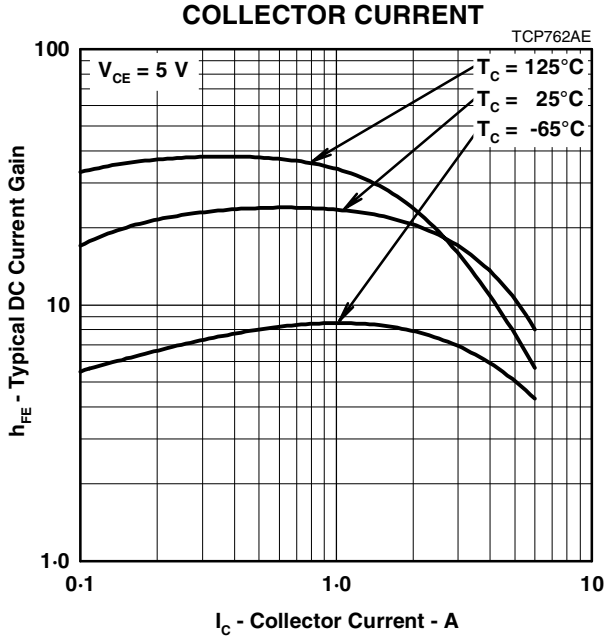


Figure 3.

COLLECTOR-EMITTER SATURATION VOLTAGE vs BASE CURRENT

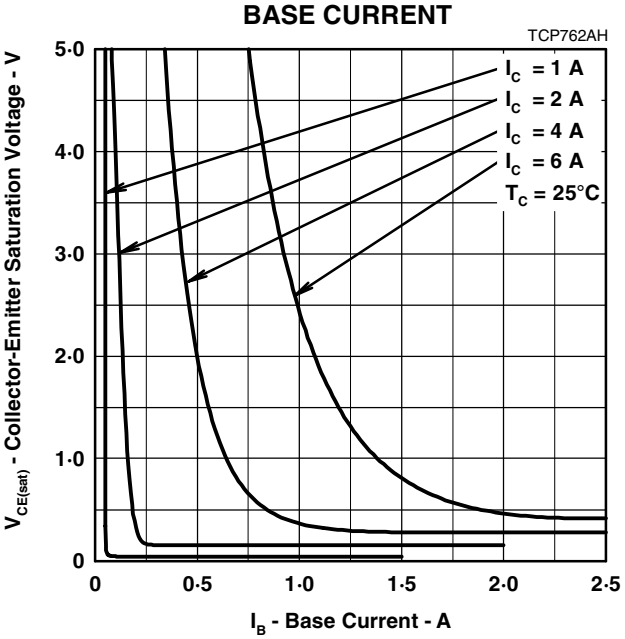


Figure 4.

COLLECTOR-EMITTER SATURATION VOLTAGE vs BASE CURRENT

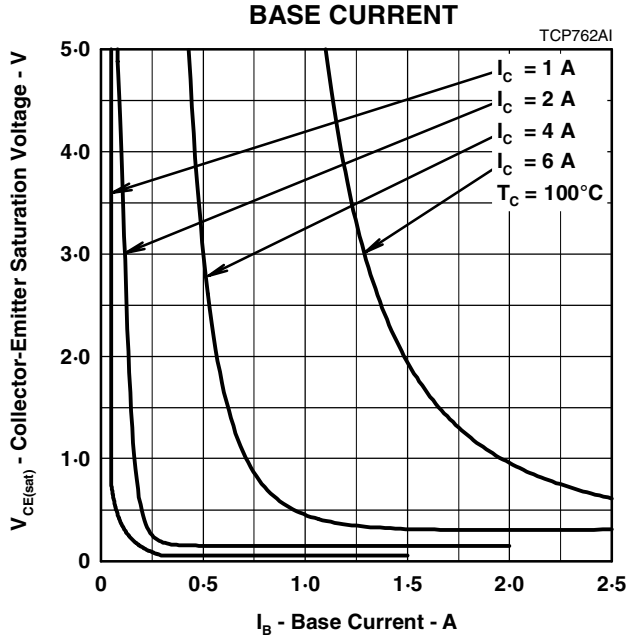


Figure 5.

BASE-EMITTER SATURATION VOLTAGE vs BASE CURRENT

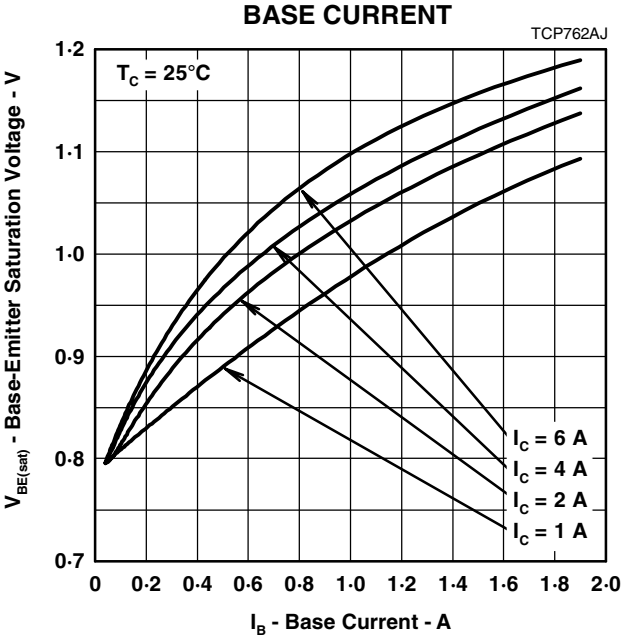


Figure 6.

TYPICAL CHARACTERISTICS

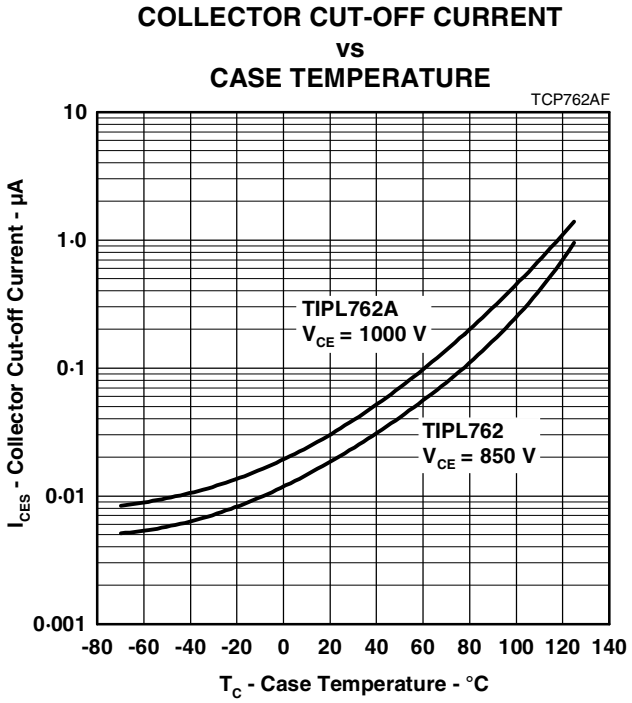


Figure 7.

MAXIMUM SAFE OPERATING REGIONS

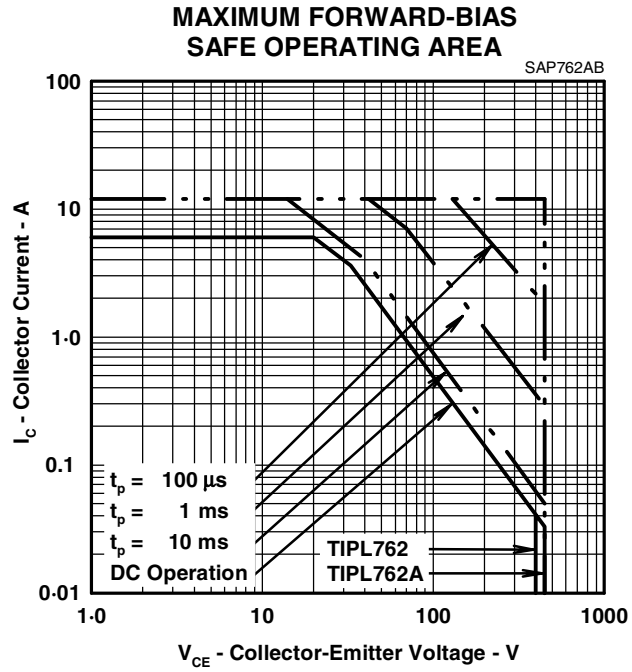


Figure 8.

THERMAL INFORMATION

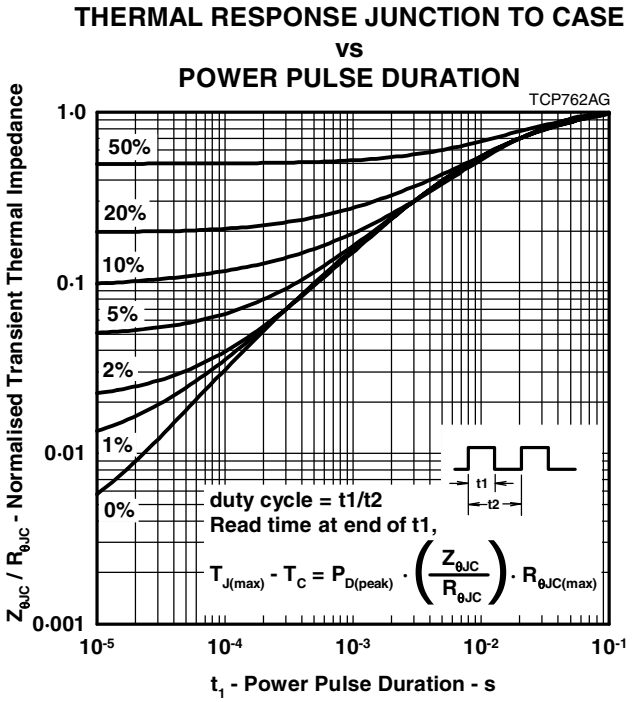


Figure 9.